



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

Liya Regel, et al

A METHOD FOR  
MANUFACTURING DIAMOND  
COATINGS

Serial No. 10/722,309

Filed 25 November 2003

Group Art Unit:

Examiner:

I hereby certify that this correspondence is being deposited today with the United States Postal Service as first class mail in an envelope addressed to Commissioner For Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

*Robin G. Reeves*  
Robin G. Reeves

*2/3/04*  
Date

Commissioner for Patents  
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Sir:

**INFORMATION DISCLOSURE STATEMENT FOR CONSIDERATION**  
**BY THE OFFICE UNDER 37 C.F.R. 1.97-1.99**

Enclosed herewith are patents and/or publications for consideration by the Patent and Trademark Office in regard to the invention claimed in the above-described application. In compliance with §1.56, such documents are listed in the enclosed Form PTO-1449.

Applicants request that the Patent and Trademark Office make of record the above-identified documents. A full text copy of each document is attached, except for copies of U.S. patents and U.S. patent application publications. For documents not in English, an English translation or an equivalent English language patent or publication may be attached. Where a translation is not available, a concise explanation of the relevance of each document not in English is included either here or in the specification.

This Information Disclosure Statement (hereinafter "Statement") is submitted according to the following selected paragraph:

- I. ☒ This Statement is being filed under §1.97(b) within three months of the filing date of the application (other than a CPA), or before the mailing of a first Office action on the merits or before the mailing of a first Office action after the filing of a request for continued examination.
- II. ☐ This Statement is being filed under §1.97(c), with fee, **prior** to the mailing date of any of a final action, a notice of allowance or an action that otherwise closes prosecution in the application. Please charge the fee required by §1.17(p) to Eastman Kodak Company Deposit Order Account Number 05-0225. A duplicate copy of this Certification is enclosed.

III. ☐ This Statement is being filed under §1.97(c), with a certification under, §1.97(e) **prior** to the mailing date of any of a final action, a notice of allowance or an action that otherwise closes prosecution in the application. The undersigned hereby states that (check one):

☐ each item of information contained in this Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement.

☐ no item of information in this Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this certification under §1.97(e) after making reasonable inquiry, no item of information contained in this Statement was known to any individual designated in §1.56(c) more than three months prior to the filing of this Statement.

IV. ☐ This Statement is being filed under §1.97(d), with fee and certification under §1.97(e), on or after the mailing date of either a final action, a notice of allowance (but prior to payment of the issue fee) or an action that otherwise closes prosecution in the application. Please charge the fee required by §1.17(p) to Eastman Kodak Company Deposit Order Account No. 05-0225. A duplicate copy of this Certification is enclosed. The undersigned hereby states that (check one):

☐ each item of information in this Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement.

☐ no item of information in this Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this certification under §1.97(e) after making reasonable inquiry, no item of information contained in this Statement was known to any individual designated in §1.56(c) more than three months prior to the filing of this Statement.

Respectfully submitted,



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Enclosures



FORM PTO-1449

US DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

Atty. Docket No.

86655SHS

Serial No.

10/722,309

Customer No. 01333

Applicant:

Liya Regel, et al

If AFTER the later date of the first Office Action or 3 months from filing, use only with Rule 97(E) Certificate or Fee

## LIST OF ART CITED BY APPLICANT

(Use several sheets if necessary)

Filing Date

25 November 2003

Group

## U.S. PATENT DOCUMENTS

Examiner Initial*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	US 2003/0173895 A1	09-18-2003	Yoshifumi Kato et al.	313	504	01-30-2003
	5,920,080	07-06-1999	Gary W. Jones	257	40	05-08-1998
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	6,608,449	08-19-2003	Takeshi Fukanaga	315	169.3	05-08-2001

## FOREIGN PATENT DOCUMENTS

Examiner Initial*	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES   NO
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## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

✓	A. Gicquel, K. Hassouni, F. Silva and J. Achard, "CVD diamond films: from growth to applications," <i>Current Applied Physics</i> 1 (2001), pp. 479-496.
	"Diamond Films" Recent Developments," Volume 23, No. 9 of the MRS Bulletin (September 1998), Materials Research Society, Warrendale, Pennsylvania.
✓	L.L. Regel and W.R. Wilcox, "Diamond film deposition by chemical vapor transport," <i>Acta Astronautica</i> 48 (2001), pp. 129-144.
✓	W.L. Wang, K.J. Liao, R.Q. Zhang and C.Y. Kong, "Investigation of organic light emitting devices using boron-doped diamond electrodes," <i>Materials Science and Engineering B85</i> (2001), pp. 169-171.
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EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

